

C¹

1. (Twice Amended) A method for the fabrication of a Schottky barrier diode on [a] an SiC wafer, comprising the steps of:

- (a) forming an insulating layer on the surface of the SiC wafer;
- (b) placing a mask having a window on an exposed surface of the insulating layer;
- (c) etching away a portion of the insulating layer corresponding to the window to expose a portion of the SiC wafer therebeneath;
- (d) while retaining the mask in place, depositing conductive material on the mask and exposed portions of the wafer surface; [and]
- (e) stripping off the mask so as to leave the conductive material deposited upon the portion of the wafer surface corresponding to the window; and
- (f) implanting an edge termination layer into the wafer beneath the surface [thereof] of the insulating layer but not beneath the conductive material.

C² cont.

18. (Amended) A method for the fabrication of a Schottky barrier diode on [a] an SiC wafer, comprising the steps of:

- (a) forming an insulating layer on a surface of the SiC wafer;
- (b) placing a mask having a window on an exposed surface of the insulating layer;
- (c) etching away a portion of the insulating layer corresponding to the window to expose the SiC wafer therebeneath;
- (d) while retaining the mask in place, depositing conductive material on the mask exposed portions of the wafer surface; [and]
- (e) stripping off the mask so as to leave the conductive material deposited upon the portion of the wafer surface corresponding to the window [.]